AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (CURRENTLY AMENDED) A method for forming a pattern, comprising:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into at least two areas;

providing a cliché on which a plurality of grooves are formed;

filling resist in the grooves; ~~and~~

~~applying the resist filled in the grooves of the cliché onto the etching object layer by the divided area of the substrate~~

transferring the resist in the grooves on a blanket applied on a surface of a printing roll by contacting and rotating the printing roll with the blanket on the cliché corresponding to the divided area of the substrate; and

applying the resist transferred on the surface of the blanket on the etching object layer.

2. (CURRENTLY AMENDED) The method of claim 1, wherein ~~applying the resist on the etching object layer comprises:~~

~~providing a~~ the printing roll ~~having~~ has a same width as that of the divided area of the substrate;

~~transferring the resist in the groove of the cliché onto a surface of the printing roll by contacting and rotating the printing roll on the cliché corresponding to the divided area of the substrate; and~~

~~applying the resist transferred on the surface of the printing roll on the etching object layer~~.

3. (CANCELED)

4. (CURRENTLY AMENDED) The method of claim ~~3~~ 2, wherein a length of the blanket is the same as a length of a circumference of the printing roll, which is same as a length of the divided area of the substrate.

5. (ORIGINAL) The method of claim 1, wherein the divided area of the substrate includes one or more unit panels.

6. (ORIGINAL) The method of claim 1, wherein the cliché is formed to have a same size as that of the divided area of the substrate.

7. (ORIGINAL) The method of claim 1, wherein the printing roll is formed to have a same size as that of the divided area on the substrate.

8. (ORIGINAL) The method of claim 1, wherein the etching object layer includes a metal layer.

9. (ORIGINAL) The method of claim 1, wherein the etching object layer includes an insulating layer comprised of SiOx or SiNx.

10. (ORIGINAL) The method of claim 1, wherein the etching object layer is a semiconductor layer.

11. (CURRENTLY AMENDED) A method for forming a pattern, comprising:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into a plurality of divided areas so as to include at least one or more unit panels;

providing a cliché on which a plurality of grooves are formed;

filling resist in the grooves of the cliché;

providing a blanket on a printing roll having a same width as that of the divided area of the substrate;

transferring the resist filled in the groove of the cliché onto a surface of the blanket on the printing roll by contacting and rotating the printing roll with the blanket on the cliché; and

applying the resist transferred on the surface of the ~~printing roll~~ blanket on the etching object layer.

12. (CURRENTLY AMENDED) The method of claim 11, wherein applying the resist on the etching object layer is performed by contacting the resist transferred on the surface of the blanket on the printing roll on the substrate and by rotating the printing roll with the blanket.

13. (ORIGINAL) The method of claim 11, wherein the divided area of the substrate includes at least one unit panel.

14. (ORIGINAL) The method of claim 11, wherein the etching object layer includes a metal layer.

15. (ORIGINAL) The method of claim 11, wherein the etching object layer comprises an insulating layer comprised of SiOx or SiNx.

16. (ORIGINAL) The method of claim 11, wherein the etching object layer is a semiconductor layer.

17. (CURRENTLY AMENDED) A pattern, which has been formed by:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into at least two areas;

providing a cliché on which a plurality of grooves are formed;

filling resist in the grooves; ~~and~~

~~applying the resist filled in the grooves of the cliché onto the etching object layer by the divided area of the substrate~~

transferring the resist in the grooves on a blanket applied on a surface of a printing roll by contacting and rotating the printing roll with the blanket on the cliché corresponding to the divided area of the substrate; and

applying the resist transferred on the surface of the blanket on the etching object layer.

18. (CURRENTLY AMENDED) A pattern, which has been formed by:

providing a substrate on which a plurality of unit panels and etching object layers on the respective unit panel areas are formed;

dividing the substrate into a plurality of divided areas so as to include at least one or more unit panels;

providing a cliché on which a plurality of grooves are formed;

filling resist in the grooves of the cliché;

providing a blanket on a printing roll having a same width as that of the divided area of the substrate;

transferring the resist filled in the groove of the cliché onto a surface of the blanket on the printing roll by contacting and rotating the printing roll with the blanket on the cliché; and

applying the resist transferred on the surface of the ~~printing roll~~ blanket on the etching object layer.

19. (NEW) A method for forming a resist pattern, comprising:

transferring a resist material from one or more grooves of a cliché onto a blanket; and

transferring the resist material from the blanket onto a surface of an etching object layer to form the resist pattern.

20. (NEW) The method of claim 19, wherein the step of transferring the resist material from the one or more grooves of the cliché onto the blanket comprises:

applying the blanket onto a surface of a printing roll; and

rolling the printing roll with the blanket on the cliché.

21. (NEW) The method of claim 20, wherein the step of transferring the resist material from the blanket onto the surface of the etching object layer to form the resist pattern comprises:

rolling the printing roll with the blanket with the resist material thereon on the surface of the etching object layer.

22. (NEW) The method of claim 20, wherein size and shape of the blanket, size and shape of the cliché, and size and shape of a surface area of the printing roll are all substantially the same.

23. (NEW) The method of claim 22, wherein

the printing roll is cylindrical,

a height of the printing roll is substantially equal to a height of the blanket, and

a circumference of the printing roll is substantially equal to a length of the blanket.

24. (NEW) The method of claim 22, wherein

the object layer is divided into a plurality of divided areas, and

the size and shape of the blanket is substantially the same as a size and shape of a sum of one or more divided areas of the plurality of divided areas.

25. (NEW) The method of claim 24, wherein size and shape of each divided area of the object layer is substantially the same in size and shape as each of the other divided areas.

26. (NEW) The method of claim 24, wherein the area of the blanket is less than an area of the etching object layer.

27. (NEW) The method of claim 26, wherein the area of the etching object layer is substantially a whole multiple of the area the blanket.